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Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l053r8h6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

3 Functional overview

3.1 Low-power modes

The ultra-low-power STM32L053x6/8 support dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

• Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

Low-power run mode

This mode is achieved with the multispeed internal (MSI) RC oscillator set to the lowspeed clock (max 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Lowpower run mode, the clock frequency and the number of enabled peripherals are both limited.

Low-power sleep mode

This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

When wakeup is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

Stop mode with RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSE crystal and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on), it can be the RTC alarm/tamper/timestamp/wakeup events, the USB/USART/I2C/LPUART/LPTIMER wakeup events.



			Low-	Low-	Stop			Standby
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
DAC	0	0	0	0	0			
Temperature sensor	0	О	0	0	0			
Comparators	0	0	0	0	0	0		
16-bit timers	0	0	0	0				
LPTIMER	0	0	0	0	0	0		
IWDG	0	0	0	0	0	0	0	0
WWDG	0	0	0	0				
Touch sensing controller (TSC)	0	О						
SysTick Timer	0	0	0	0				
GPIOs	0	0	0	0	0	0		2 pins
Wakeup time to Run mode	0 µs	0.36 µs	3 µs	32 µs	3.5 µs		50 µs	
			0. RTC	4 µA (No) V _{DD} =1.8 V	0.1 RTC	28 µA (No) V _{DD} =1.8 V		
Consumption	Down to 140 µA/MHz (from Flash memory)	Down to 37 µA/MHz (from Flash memory)	Down to	Down to	0.8 µA (with RTC) V _{DD} =1.8 V		0.6 RTC	5 μΑ (with) V _{DD} =1.8 V
(Typ)			8 μΑ	4.5 µA	0.4 µA (No RTC) V _{DD} =3.0 V		0. RTC	29 µA (No) V _{DD} =3.0 V
					1 μΑ 	(with RTC) _{DD} =3.0 V	0.8 RTC	85 μΑ (with) V _{DD} =3.0 V

Table 4. Functionalities depending on the working mode (from Run/active down to standby) (continued)⁽¹⁾

Legend: "Y" = Yes (enable). "O" = Optional can be enabled/disabled by software) "-" = Not available

Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the
peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need
it anymore.

3. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start. To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.

4. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.



3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Interconnect Interconnect source destination Interconnect a		Interconnect action	Run	Sleep	Low- power run	Low- power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	-
	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	Y
TIMx TIMx Time		Timer triggered by other timer	Y	Y	Y	Y	-
RTC	TIM21	Timer triggered by Auto wake-up	Y	Y	Y	Y	-
	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Y
All clock source TIMx		Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-
USB CRS/HSI48 sys b		the clock recovery system trims the HSI48 based on USB SOF	Y	Y	-	-	-
	TIMx	Timer input channel and trigger	Y	Y	Y	Y	-
GPIO	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC,DAC	Conversion trigger	Y	Y	Y	Y	-

Table 5. STM32L0xx peripherals interconnect matrix



3.16 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21, TIM22 and LPTIM timer input captures. It also controls the routing of internal analog signals to the USB internal oscillator, ADC, COMP1 and COMP2 and the internal reference voltage V_{REFINT} .

3.17 Touch sensing controller (TSC)

The STM32L053x6/8 provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (such as glass, plastic). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage, this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
	TSC_G1_IO1	PA0		TSC_G5_IO1	PB3
1	TSC_G1_IO2	PA1	5	TSC_G5_IO2	PB4
I	TSC_G1_IO3	PA2	5	TSC_G5_IO3	PB6
	TSC_G1_IO4	PA3		TSC_G5_IO4	PB7
	TSC_G2_IO1	PA4 ⁽¹⁾		TSC_G6_IO1	PB11
2	TSC_G2_IO2	PA5	6	TSC_G6_IO2	PB12
2	TSC_G2_IO3	PA6	0	TSC_G6_IO3	PB13
	TSC_G2_IO4	PA7		TSC_G6_IO4	PB14
	TSC_G3_IO1	PC5		TSC_G7_IO1	PC0
2	TSC_G3_IO2	PB0	7	TSC_G7_IO2	PC1
5	TSC_G3_IO3	PB1		TSC_G7_IO3	PC2
	TSC_G3_IO4	PB2		TSC_G7_IO4	PC3



5 Memory mapping



Figure 6. Memory map



6.3 Operating conditions

6.3.1 General operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit	
f _{HCLK}	Internal AHB clock frequency	-	0	32		
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	MHz	
f _{PCLK2}	Internal APB2 clock frequency	-	0	32		
		BOR detector disabled	1.65	3.6	v	
V _{DD}	Standard operating voltage	BOR detector enabled, at power-on	1.8	3.6		
		BOR detector disabled, after power-on	1.65	3.6		
V _{DDA}	Analog operating voltage (DAC not used)	Must be the same voltage as $V_{DD}^{(1)}$	1.65	3.6	V	
V _{DDA}	Analog operating voltage (all features)	Must be the same voltage as $V_{DD}^{(1)}$	1.8	3.6	V	
V _{DD US}	Standard operating voltage, USB	USB peripheral used	3.0	3.6	V	
B	domain ⁽²⁾	USB peripheral not used	1.65	3.6	V	
V _{IN}	Input voltage on ET ETf and PST pipe ⁽³⁾	2.0 V ≤V _{DD} ≤3.6 V	-0.3	5.5		
		1.65 V ≤V _{DD} ≤2.0 V	-0.3	5.2	V	
	Input voltage on BOOT0 pin	-	0	5.5		
	Input voltage on TC pin	-	-0.3	V _{DD} +0.3		
		TFBGA64 package	-	327		
	Power dissipation at $T_A = 85 \text{ °C}$ (range 6) or $T_A = 105 \text{ °C}$ (rage 7) ⁽⁴⁾	LQFP64 package	-	444	mW	
Б		LQFP48 package	-	363		
' D		TFBGA64 package	-	81		
	Power dissipation at T _A = 125 °C (range 3) ⁽⁴⁾	LQFP64 package	-	111	_	
	-,	LQFP48 package	-	91		
		Maximum power dissipation (range 6)	-40	85		
ΤΑ	Temperature range	Maximum power dissipation (range 7)	-40	105		
		Maximum power dissipation (range 3)	-40	125	°C	
	Junction temperature range (range 6)	-40 °C ≤T _A ≤85 °	-40	105		
TJ	Junction temperature range (range 7)	-40 °C ≤T _A ≤105 °C	-40	125		
	Junction temperature range (range 3)	-40 °C ≤T _A ≤125 °C	-40	130		

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.



- 2. V_{DD_USB} must respect the following conditions:
- When V_{DD} is powered-on (V_{DD} < V_{DD} min), V_{DD} USB should be always lower than V_{DD}.
- When V_{DD} is powered-down (V_{DD} < V_{DD} min), V_{DD} USB should be always lower than V_{DD}.
- In operating mode, V_{DD_USB} could be lower or higher $V_{DD.}$
- If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os.
- 3. To sustain a voltage higher than $V_{\text{DD}}\text{+}0.3\text{V},$ the internal pull-up/pull-down resistors must be disabled.
- 4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see *Table 85: Thermal characteristics on page 123*).



Symbol	Parameter	Condition	Тур	Max	Unit	
ACC _{MSI}	Frequency error after factory calibration	-	±0.5	-	%	
	MSI oscillator frequency drift 0 °C ≤T _A ⊴85 °C	- ±3		-		
		MSI range 0	- 8.9	+7.0		
		MSI range 1	- 7.1	+5.0		
D _{TEMP(MSI)} ⁽¹⁾		MSI range 2	- 6.4	+4.0	%	
	MSI oscillator frequency drift V _{DD} = 3.3 V. − 40 °C ≤T ₄ ≤110 °C	MSI range 3	- 6.2	+3.0		
		MSI range 4	- 5.2	+3.0		
		MSI range 5	- 4.8	+2.0		
		MSI range 6	- 4.7	+2.0		
D _{VOLT(MSI)} ⁽¹⁾	MSI oscillator frequency drift 1.65 V ≤V _{DD} ≤3.6 V, T _A = 25 °C	-	-	2.5	%/V	
		MSI range 0	0.75	-		
I _{DD(MSI)} ⁽²⁾		MSI range 1	1	-		
		MSI range 2	1.5	-	μA	
	MSI oscillator power consumption	MSI range 3	2.5	-		
		MSI range 4	4.5	-		
		MSI range 5	8	-		
		MSI range 6	15	-		
		MSI range 0	30	-		
		MSI range 1	20	-		
		MSI range 2	15	-]	
		MSI range 3	10	-	μs	
t	MSL oscillator startun time	MSI range 4	6	-		
^I SU(MSI)		MSI range 5	5	-		
		MSI range 6, Voltage range 1 and 2	3.5	-		
		MSI range 6, Voltage range 3	5	-		

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6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	$T_A = +25 \text{ °C},$ conforming to ANSI/JEDEC JS-001	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	$T_A = +25 \text{ °C},$ conforming to ANSI/ESD STM5.3.1.	C4	500	v

Table 55. ESD absolute maximum ratings

1. Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 56. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +125$ °C conforming to JESD78A	II level A



6.3.16 DAC electrical characteristics

Data guaranteed by design, not tested in production, unless otherwise specified.

Symbol	Parameter	Cond	litions	Min	Тур	Мах	Unit		
V _{DDA}	Analog supply voltage	-		1.8	-	3.6	V		
V _{REF+}	Reference supply voltage	V _{REF+} must always be below V _{DDA}		V_{REF^+} must always be below V_{DDA}		1.8	-	3.6	V
V _{REF-}	Lower reference voltage	-		-			V _{SSA}		V
I _{DDVREF+} ⁽¹⁾	Current consumption on V _{REF+}	No load, mid (0x800)	dle code	-	130	220			
	V _{REF+} = 3.3 V	No load, wor (0x000)	st code	-	220	350	μA		
(2)	(2) Current consumption on V _{DDA}		Current consumption on V _{DDA} No load, middle code (0x800)		-	210	320		
DDA	$V_{DDA} = 3.3 V$	No load, worst code (0xF1C)		-	320	520	μΛ		
R _L ⁽³⁾	Resistive load	DAC output	R _L connected to V _{SSA}	5	-	-	kΩ		
		ON	R _L connected to V _{DDA}	25	-	-			
C _L ⁽³⁾	Capacitive load	DAC output	buffer ON	-	-	50	pF		
R _O	Output impedance	DAC output buffer OFF		12	16	20	kΩ		
		DAC output buffer ON		0.2	-	V _{DDA} – 0.2	V		
VDAC_OUT		DAC output buffer OFF		0.5	-	V _{REF+} – 1LSB	mV		

Table 65. DAC characteristics



6.3.19 Timer characteristics

TIM timer characteristics

The parameters given in the Table 70 are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

,					
Symbol	Parameter	Conditions	Min	Мах	Unit
t ann	Timer resolution time		1	-	t _{TIMxCLK}
۲es(TIM)		f _{TIMxCLK} = 32 MHz	31.25	-	ns
f	Timer external clock frequency on CH1		0	f _{TIMxCLK} /2	MHz
'EXT	to CH4	f _{TIMxCLK} = 32 MHz	0	16	MHz
Res _{TIM}	Timer resolution	-		16	bit
	16-bit counter clock period when	-	1	65536	t _{TIMxCLK}
^t COUNTER	internal clock is selected (timer's prescaler disabled)	f _{TIMxCLK} = 32 MHz	0.0312	2048	μs
	Maximum possible count	-	-	65536 × 65536	t _{TIMxCLK}
'MAX_COUNT		f _{TIMxCLK} = 32 MHz	-	134.2	S

Table 70. TIMx characteristics⁽¹⁾

1. TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

6.3.20 Communications interfaces

I²C interface characteristics

The I^2C interface meets the timings requirements of the I^2C -bus specification and user manual rev. 03 for:

- Standard-mode (Sm) : with a bit rate up to 100 kbit/s
- Fast-mode (Fm) : with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+) : with a bit rate up to 1 Mbit/s.

The I²C timing requirements are guaranteed by design when the I²C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to *Section 6.3.13: I/O port characteristics* for the I2C I/Os characteristics).

All I²C SDA and SCL I/Os embed an analog filter (see *Table 71* for the analog filter characteristics).





Figure 34. I²S slave timing diagram (Philips protocol)⁽¹⁾

- 1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



Figure 35. I²S master timing diagram (Philips protocol)⁽¹⁾

- 1. Guaranteed by characterization results.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



Symbol	millimeters			inches ⁽¹⁾		
	Min	Тур	Мах	Min	Тур	Мах
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-
е	-	0.500	-	-	0.0197	-
К	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
CCC	-	-	0.080	-	-	0.0031

Table 81. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.



Device marking for LQFP64

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.





7.2 TFBGA64 package information



Figure 40. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline

1. Drawing is not to scale.

Table 82. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Тур	Max	Min	Тур	Max
А	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-



Device marking for TFBGA64

The following figure gives an example of topside marking versus ball A 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





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Device marking for LQFP48

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





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9 Revision history

Date	Revision	Changes
07-Feb-2014	1	Initial release.
29-Apr-2014	2	 Updated Table 4: Functionalities depending on the working mode (from Run/active down to standby). Added Section 3.2: Interconnect matrix. Updated Figure 4: STM32L053x6/8 TFBGA64 ballout - 5x 5 mm. Added VREF_OUT additional function to PB0 and PB1, replaced TTa I/O structure by TC, and updated PA0/4/5 and PC5/14 I/O structure, and added note 2 in Table 15: STM32L053x6/8 pin definitions. Updated Table 24: General operating conditions, Table 21: Voltage characteristics and Table 22: Current characteristics. Modified conditions in Table 27: Embedded internal reference voltage. Updated Table 28: Current consumption in Run mode, code with data processing running from Flash, Table 30: Current consumption in Run mode, code with data processing running from RAM, Table 32: Current consumption in Low-power sleep mode, Table 34: Current consumption in Low-power sleep mode, Table 36: Typical and maximum current consumptions in Standby mode. Added Figure 12: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 13: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 13: IDD vs VDD, at TA= 25/55/85/105 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 11: HS116 minimum and maximum value versus temperature. Updated Table 55: ESD absolute maximum ratings, Table 57: I/O current injection susceptibility, Table 58: I/O static characteristics. Added Figure 22: VIH/VIL versus VDD (CMOS I/Os) and Figure 23: VIH/VIL versus VDD (TTL I/Os). Updated Table 52: ADC characteristics, Table 60: I/O AC characteristics. Added Figure 24: I/O AC characteristics definition.

Table 87	. Document	revision	history
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Date	Revision	Changes		
		Updated all pinout/ballout schematics to highlight pin/ball supplied		
		Updated current consumption in Run mode in Section : Features.		
		Renamed BOOT1 into nBOOT1.		
		Changed USARTx_RTS into USARTx_RTS_DE and LPUARTx_RTS into LPUARTx_RTS_DE.		
		Updated VLCD in Section 3.12: Analog-to-digital converter (ADC)		
	5	ADC no more available in Low-power run and Low-power Sleep modes in <i>Table 4: Functionalities depending on the working mode (from</i> <i>Run/active down to standby)</i> .		
		Updated Figure 3: STM32L053x6/8 LQFP64 pinout - 10 x 10 mm, Figure 4: STM32L053x6/8 TFBGA64 ballout - 5x 5 mm and Figure 5: STM32L053x6/8 LQFP48 pinout - 7 x 7 mm. Changed I/O structure for PC5 and modified E5 and E6 signals for TFBGA64 in Table 15: STM32L053x6/8 pin definitions.		
		Added ΣI_{VDD_USB} and updated $\Sigma I_{IO(PIN)}$ in <i>Table 22: Current characteristics</i>		
		Updated V _{DD_USB} in <i>Table 22: Current characteristics</i>		
		Changed temperature condition in <i>Table 7: Internal voltage reference</i> <i>measured values</i> and <i>Table 26: Embedded internal reference voltage</i> <i>calibration values</i> .		
		Updated T _{Coeff} in <i>Table 27: Embedded internal reference voltage</i> .		
08-Sep-2015		Added note related to Standby mode in <i>Table 39: Peripheral current consumption in Stop and Standby mode</i> .		
		Updated Figure 14: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Low- power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 15: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF.		
		Updated Table 40: Low-power mode wakeup timings.		
		Updated MSI oscillator temperature frequency drift in <i>Table 48: MSI oscillator characteristics</i> .		
		Updated Table 62: ADC characteristics, Table 54: EMI characteristics and Table 55: ESD absolute maximum ratings.		
		Added t _{UP_LDO} in <i>Table 62: ADC characteristics</i> .		
		Updated <i>Table 57: I/O current injection susceptibility</i> , <i>Table 58: I/O static characteristics</i> (I _{lkg}) and <i>Table 60: I/O AC characteristics</i> .		
		Section : I2C interface characteristics: updated introduction and Table 71: I2C analog filter characteristics.		
		Updated Figure 31: SPI timing diagram - slave mode and CPHA = 0.		
		Added Section : Device marking for LQFP64, updated Figure 42: TFBGA64 marking example (package top view) and Figure 45: LQFP48 marking example (package top view) as well as notes below		
		schematics.		



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